



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

Digital transistors (built-in resistors)

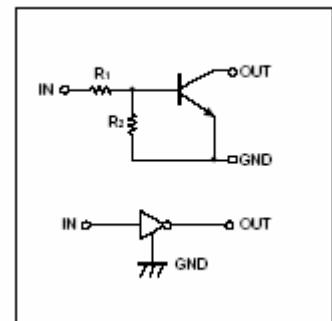
DTC114EE/DTC114EUA /DTC114EKA /DTC114ECA /DTC114ESA

DIGITAL TRANSISTOR (NPN)

FEATURES

1. Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
2. The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
3. Only the on/off conditions need to be set for operation, making device design easy.

● Equivalent circuit



PIN CONNECTIONS AND MARKING

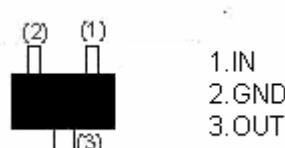
DTC114EE



SOT-523

Addreviated symbol: 24

DTC114EUA

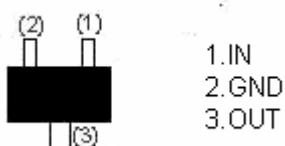


1.IN
2.GND
3.OUT

SOT-323

Addreviated symbol: 24

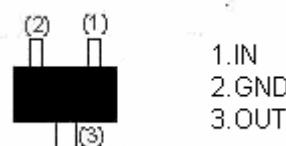
DTC114EKA



SOT-23-3L

Addreviated symbol: 24

DTC114ECA

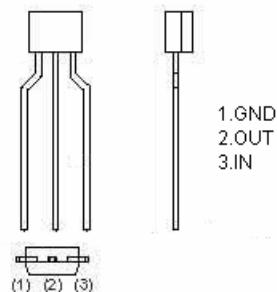


1.IN
2.GND
3.OUT

SOT-23

Addreviated symbol: 24

DTC114ESA



TO-92S

DTC114EE	DTC114EUA	DTC114EKA	DTC114ECA
SOT-523 Addreviated symbol: 24	SOT-323 Addreviated symbol: 24	SOT-23-3L Addreviated symbol: 24	SOT-23 Addreviated symbol: 24
DTC114ESA	DTC114EUA	DTC114EKA	DTC114ECA
TO-92S	SOT-323	SOT-23-3L	SOT-23

Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits (DTC114E□)					Unit				
		E	UA	CA	KA	SA					
Supply voltage	V _{CC}	50					V				
Input voltage	V _{IN}	-10~40					V				
Output current	I _O	50					mA				
	I _{C(MAX)}	100									
Power dissipation	P _d	150	200		300		mW				
Junction temperature	T _j	150					°C				
Storage temperature	T _{stg}	-55~150					°C				

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	V _{I(off)}			0.5	V	V _{CC} =5V ,I _O =100μA
	V _{I(on)}	3				V _O =0.3V ,I _O =10 mA
Output voltage	V _{O(on)}			0.3	V	I _O /I _I =10mA/0.5mA
Input current	I _I			0.88	mA	V _I =5V
Output current	I _{O(off)}			0.5	μA	V _{CC} =50V, V _I =0
DC current gain	G _I	30				V _O =5V ,I _O =5mA
Input resistance	R _I	7	10	13	KΩ	
Resistance ratio	R ₂ /R ₁	0.8	1	1.2		
Transition frequency	f _T		250		MHz	V _O =10V ,I _O =5mA,f=100MHz

Typical Characteristics

●Electrical characteristic curves

